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Red – Plasma Etching Blue – Advanced Devices

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| US Patent Nr. | Title | Assignee | Filed | Date of Patent |
|---------------|---|---|----------|----------------|
| 6,642,151 | Techniques for plasma etching silicon-germanium | Applied Materials, Inc | 3/6/02 | 11/4/03 |
| 6,642,566 | Asymmetric inside spacer for vertical transistor | International Business Machines Corporation | 6/28/02 | 11/4/03 |
| 6,645,795 | Polysilicon doped transistor using silicon-on- insulator and double silicon-on-insulator | International Business Machines Corporation | 5/3/01 | 11/11/03 |
| 6,649,075 | Method and apparatus for measuring etch uniformity of a semiconductor wafer | Applied Materials, Inc. | 7/23/96 | 11/18/03 |
| 6,650,426 | Endpoint determination for recess etching to a precise depth | SC Technology, Inc. | 7/12/00 | 11/18/03 |
| 6,653,231 | Process for reducing the critical dimensions of integrated circuit device features | Advanced Micro Devices, Inc. | 3/28/01 | 11/25/03 |
| 6,653,698 | Integration of dual workfunction metal gate CMOS devices | International Business Machines Corporation | 12/20/01 | 11/25/03 |

Clarycon: Plasma Technology for Advanced Devices

| 6,653,734 | Convertible hot edge ring to improve low-K dielectric etch | Lam Research Corporation | 1/30/02 | 11/25/03 |
|-----------|---|---|---------|----------|
| 6,656,808 | Transistor having variable width gate electrode and method of manufacturing the same | Samsung Electronics Co., Ltd. | 9/5/01 | 12/2/03 |
| 6,656,824 | Low resistance T-gate MOSFET device using a damascene gate process and an innovative oxide removal etch | International Business Machines Corporation | 11/8/02 | 12/2/03 |
| 6,656,847 | Method for etching silicon nitride selective to titanium silicide | Taiwan Semiconductor Manufacturing Company | 1/1/99 | 12/2/03 |
| 6,656,850 | Method for in-situ removal of side walls in MOM capacitor formation | Agere Systems Inc. | 8/8/02 | 12/2/03 |
| 6,657,259 | Multiple-plane FinFET CMOS | International Business Machines Corporation | 12/4/01 | 12/2/03 |
| 6,657,267 | Semiconductor device and fabrication technique using a high-K liner for spacer etch stop | Advanced Micro Devices, Inc. | 6/6/02 | 12/2/03 |